

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO220 plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{j(max)} = 150\text{ °C}$).

2. Features and benefits

- AC power control
- High blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant
- IEC 61000-4-4 fast transient

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

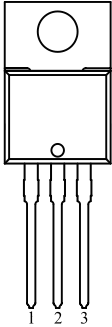

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 129\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	30	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig 4 ; Fig 5	350	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	385	A
T_j	junction temperature		150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7	6	-	15	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	-	60	mA
V_T	on-state voltage	$I_T = 60\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.3	1.5	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 150\text{ °C}$; exponential waveform; gate open circuit	1000	-	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		 sym037
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

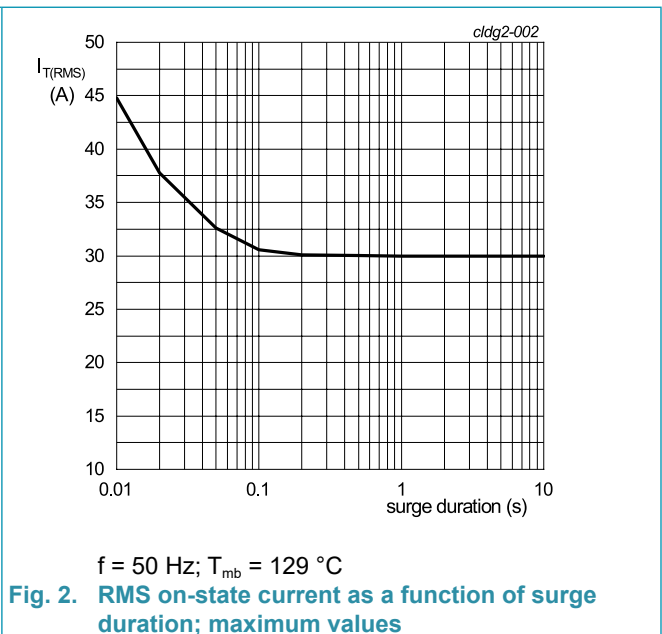
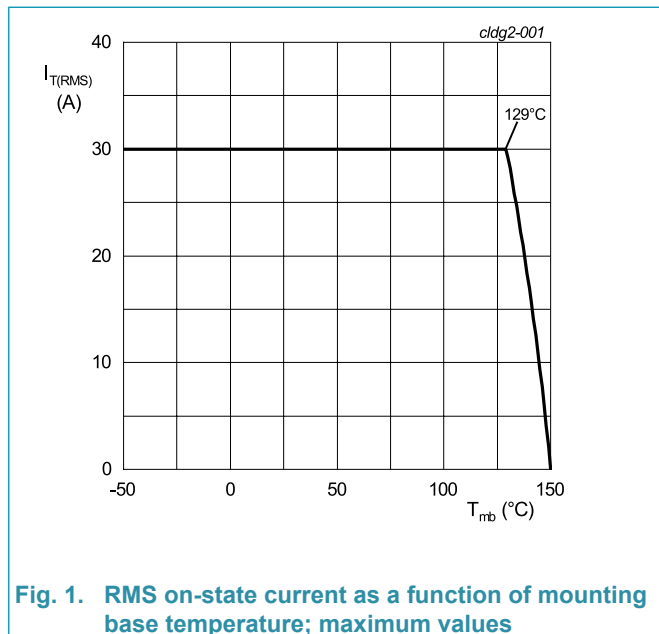
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN30-800T	TO220	TYN30-800TQ	Tube	50	TO220E	26-April-2019

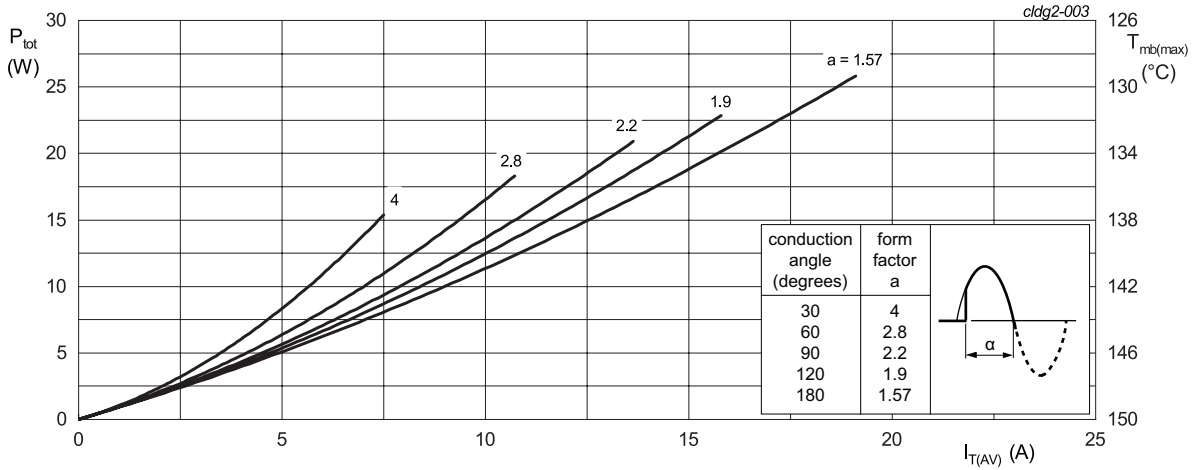
7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

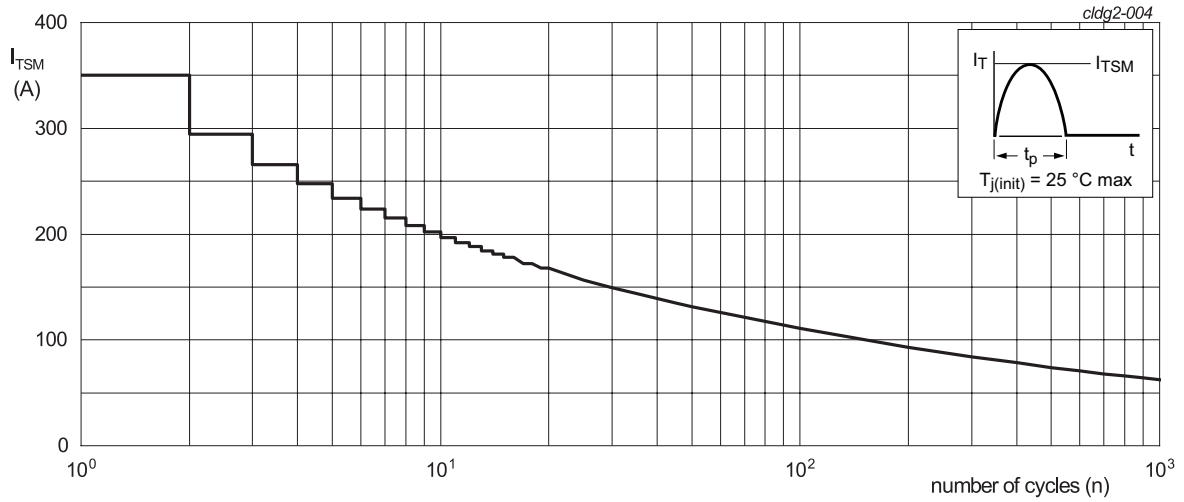
Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
V_{RRM}	repetitive peak reverse voltage		800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 129\text{ }^{\circ}\text{C}$;	19	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 129\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	30	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig 4 ; Fig 5	350	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	385	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	612.5	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 30\text{ mA}$	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		5	A
V_{GM}	peak gate voltage		5	V
P_{GM}	peak gate power		20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	$^{\circ}\text{C}$
T_j	junction temperature		150	$^{\circ}\text{C}$





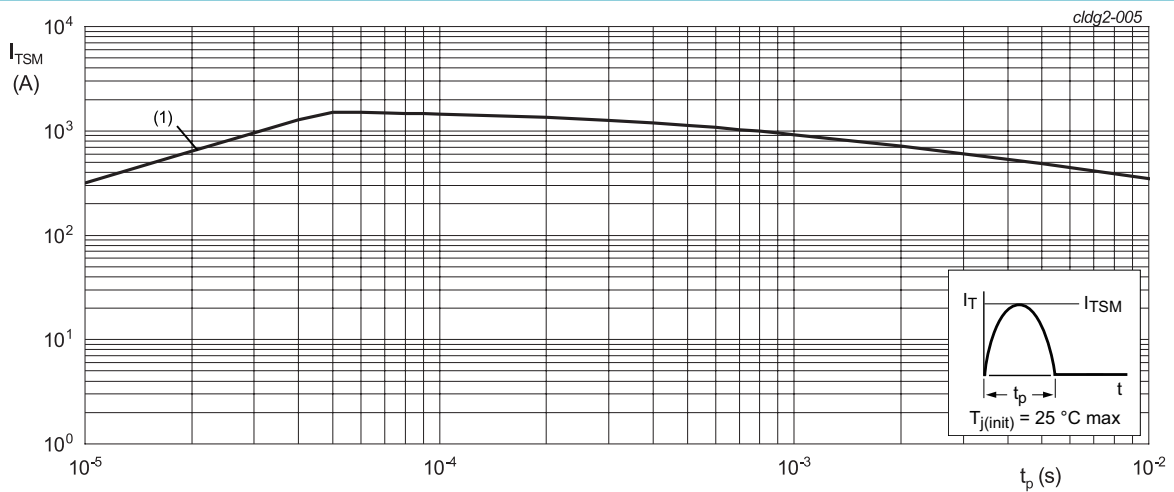
α = conduction angle
 a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



$f = 50\text{ Hz}$

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 10\text{ ms}$
 (1) di_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig 6	-	-	0.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

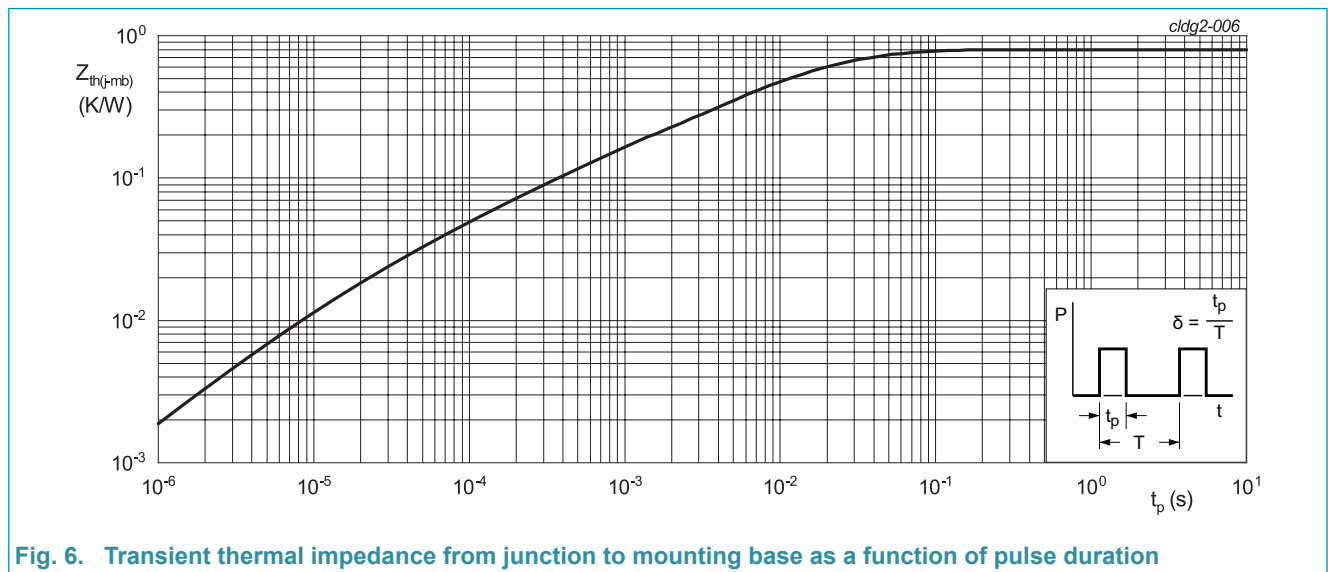
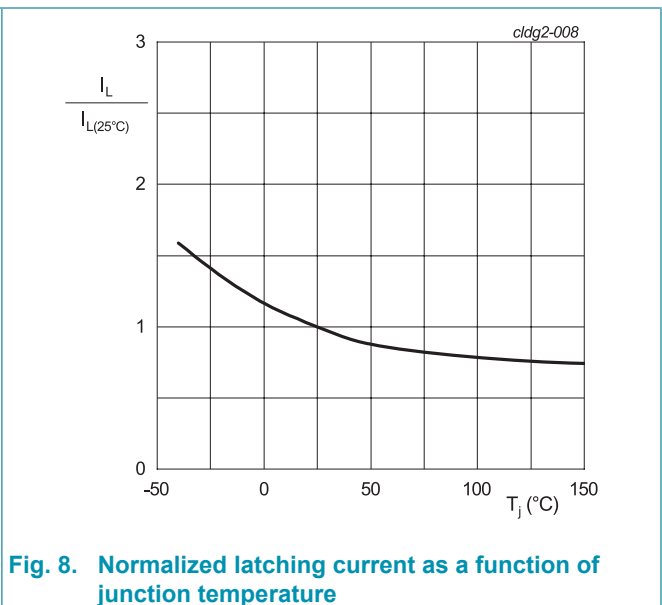
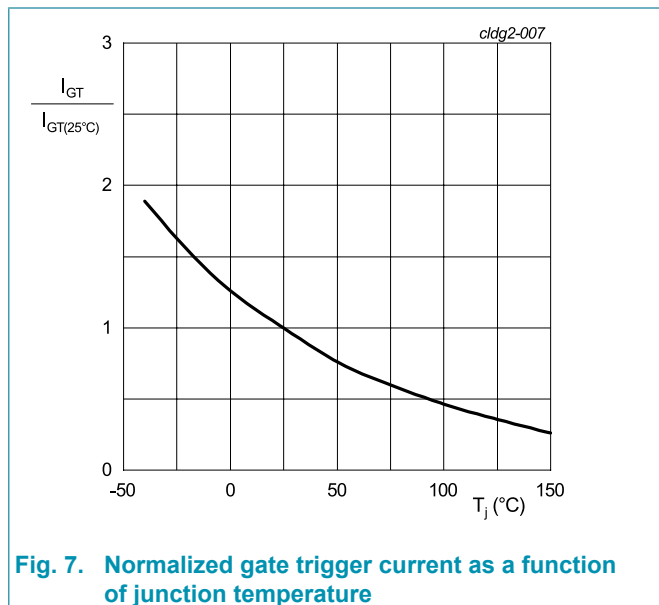


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 7	6	-	15	mA
I_L	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	80	mA
I_H	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	-	60	mA
V_T	on-state voltage	$I_T = 60\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	0.6	1	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.25	0.4	-	V
I_D	off-state current	$V_D = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	1	mA
I_R	reverse current	$V_R = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	1	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 150\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	1000	-	-	V/ μs
		$V_{DM} = 536\text{ V}; T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 30\text{ A}; V_D = 800\text{ V}; I_G = 100\text{ mA}$; $di_G/dt = 5\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$	-	2	-	μs
t_q	commutated turn-off time	$V_{DM} = 536\text{ V}; T_j = 150\text{ }^\circ\text{C}$; $I_{TM} = 30\text{ A}$; $V_R = 25\text{ V}$; $di_T/dt = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$	-	70	-	μs



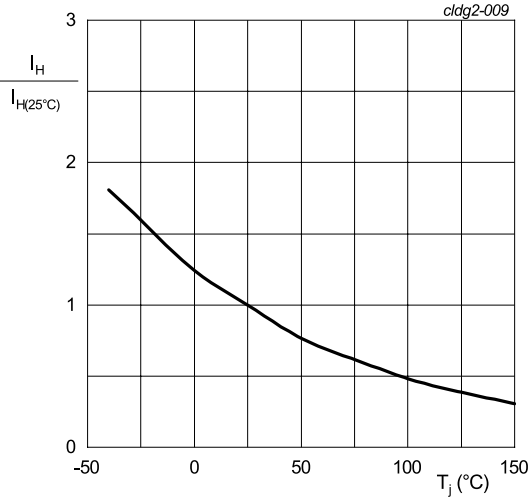
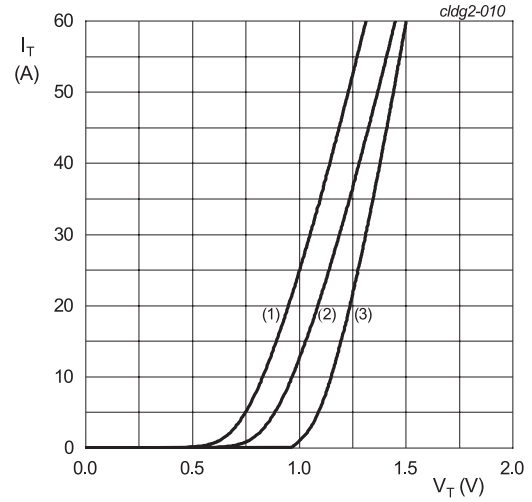


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.899 \text{ V}$; $R_s = 0.0096 \Omega$
 (1) $T_j = 150^\circ\text{C}$; typical values
 (2) $T_j = 150^\circ\text{C}$; maximum values
 (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

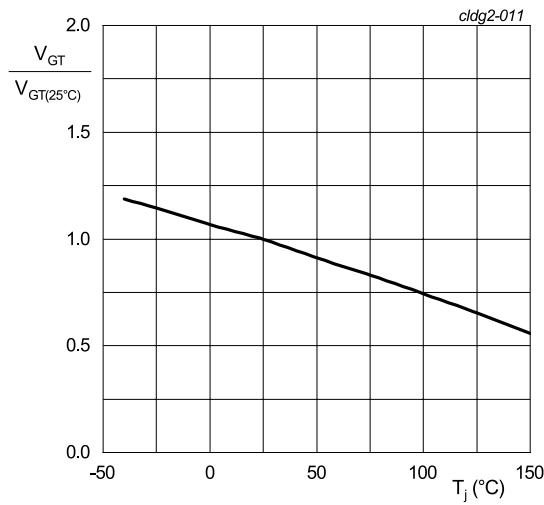
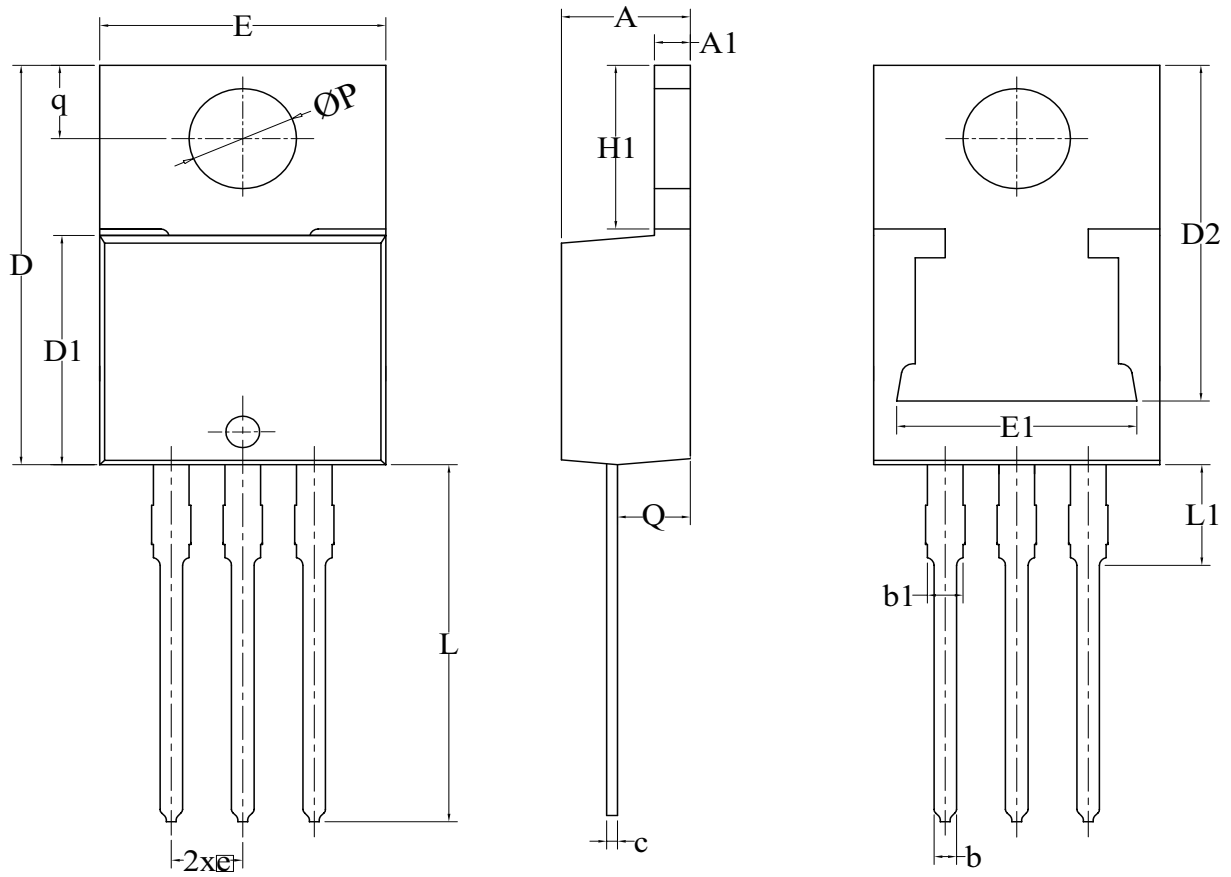


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3 leads TO-220AB TO220



Unit	A	A1	b	b1	c	D	D1	D2	E	E1	e	H1	L	L1	P	Q	q
MM	min	4.35	1.14	0.69	1.20	0.36	14.95	8.50	12.20	10.00	8.25	6.00	13.00	3.40	3.70	2.40	2.60
	max	4.75	1.40	1.01	1.45	0.61	15.55	9.02	12.88	10.40	8.89	6.40	14.00	3.80	3.95	2.80	3.00

Fig. 12. Package outline TO220

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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